Please amend the claims to read as follows:

1. (currently amended) A CVD precursor composition for forming a thin film dielectric on a substrate, such precursor composition including at least one metalloamide source reagent compound having a formula:

$M(NR_2)_x(NR'_2)_y$

wherein M is selected from the group consisting of: ~~Hf,~~ Y, La, ~~Lanthanide series elements,~~ and Ta~~, and Al~~; N is nitrogen each of R and R' is independently selected from the group consisting of H, aryl, perfluoroaryl, C_1-C_8 alkyl, C_1-C_8 perfluoroalkyl, and alkylsilyl; **x and y are different amino ligands;** x is from 1 to 5; y is from 1 to 5; and x+y is equal to the oxidation state of metal M.

2. (previously amended) The CVD precursor composition according to claim 1, wherein at least one of x is NMe_2.

3. (previously amended) The CVD precursor composition according to claim 1, wherein at least one of x is NEt_2.

4. (canceled)

Claim 5 canceled herein.

Claims 6 and 7 previously canceled.

8. (original) The CVD precursor composition according to claim 1, wherein the precursor composition further comprises a solvent medium selected from the group consisting of: ethers, glymes, tetraglymes, amines, polyamines, alcohols, glycols, aliphatic hydrocarbon solvents, aromatic hydrocarbon solvents, cyclic ethers and combinations of two or more of the foregoing.

9. (previously amended) The CVD precursor composition according to claim 5, wherein the precursor composition further comprises a solvent medium selected from the group consisting of: ethers, glymes, tetraglymes, amines, polyamines, alcohols, glycols, aliphatic hydrocarbon

solvents, aromatic hydrocarbon solvents, cyclic ethers and combinations of two or more of the foregoing.

10. (previously amended) The CVD precursor composition according to claim 8, wherein the solvent is octane.

11. (original) The CVD precursor composition according to claim 1, wherein the metalloamide source reagent compound is injected by liquid delivery into a chemical vapor deposition chamber.

12. (original) The CVD precursor composition according to claim 1, wherein the metalloamide source reagent compounds is delivered by bubbler into a chemical vapor deposition chamber.

Claims 13-15 previously canceled.

16. (original) The CVD precursor composition according to claim 1, wherein the precursor composition comprises multiple metalloamide source reagent compounds.

Claims 17-36 previously canceled.

37. (previously amended) A CVD precursor composition for forming a thin film dielectric on a substrate, such precursor composition including a vapor source reagent mixture including a metalloamide source reagent compound having a formula:

$M(NR_2)_x(NR'_2)_y$

wherein M is selected from the group consisting of: ~~Hf,~~ Y, La, ~~Lanthanide series elements,~~ and Ta~~, and Al~~; N is nitrogen each of R and R' is independently selected from the group consisting of H, aryl, perfluoroaryl, C_1-C_8 alkyl, C_1-C_8 perfluoroalkyl, and alkylsilyl; **x and y are different amino ligands;** x is from 1 to 5; y is from 1 to 5; and x+y is equal to the oxidation state of metal M.

Claims 38-85 previously canceled.

Claim 86 is currently canceled.

87. (new) A CVD precursor composition for forming a thin film dielectric on a substrate, such precursor composition including at least one metalloamide source reagent compound having a formula:

$M(NR^1R^2)_x$

wherein M is selected from the group consisting of: Hf, Y, La, Lanthanide series elements, and Ta; N is nitrogen each of R^1 and R^2 is independently selected from the group consisting of H, aryl, perfluoroaryl, C_1-C_8 alkyl, C_1-C_8 perfluoroalkyl, and alkylsilyl; x is from 1 to 5 and equal to the oxidation state of metal M.

88. (new) The CVD precursor composition of claim 87, wherein M is Ta.

89. (new) The CVD precursor composition of claim 87, wherein M is Y

90. (new) The CVD precursor composition of claim 88, selected from the group consisting of $Ta(NEt_2)_5$, $Ta(NEt_2)_5$, $Ta(NMeEt)_5$, and $Ta(NMe_2)_5$.

91. (new) The CVD precursor composition of claim 87, selected from the group consisting of $Y(NMe_2)_3$ and $Y(NEt_2)_3$.